BarıÅ Kınacı

List of Publications by Year in descending order

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840776 794594 22 374 11 19 citations h-index g-index papers 22 22 22 302 docs citations times ranked citing authors all docs

#	Article	IF	CITATIONS
1	The effect of thickness on surface structure of rf sputtered TiO2 thin films by XPS, SEM/EDS, AFM and SAM. Vacuum, 2020, 182, 109766.	3.5	68
2	Analysis of the forward and reverse bias <i>I-V</i> characteristics on Au/PVA:Zn/n-Si Schottky barrier diodes in the wide temperature range. Journal of Applied Physics, 2011, 109, .	2.5	48
3	The temperature dependent analysis of Au/TiO2 (rutile)/n-Si (MIS) SBDs using current–voltage–temperature (l–V–T) characteristics. Materials Science in Semiconductor Processing, 2012, 15, 531-535.	4.0	36
4	Performance evaluation of a GaInP/GaAs solar cell structure with the integration of AlGaAs tunnel junction. Solar Energy Materials and Solar Cells, 2015, 137, 1-5.	6.2	36
5	Design and fabrication of a semi-transparent solar cell considering the effect of the layer thickness of MoO3/Ag/MoO3 transparent top contact on optical and electrical properties. Scientific Reports, 2021, 11, 13079.	3.3	25
6	AZO thin film-based UV sensors: effects of RF power on the films. Applied Physics A: Materials Science and Processing, 2015, 119, 965-970.	2.3	24
7	Analysis of the Temperature Dependence of the Capacitance–Voltage and Conductance–Voltage Characteristics of Au/TiO2(rutile)/n-Si Structures. Journal of Electronic Materials, 2013, 42, 1108-1113.	2.2	21
8	A comprehensive study on Cu-doped ZnO (CZO) interlayered MOS structure. Journal of Materials Science: Materials in Electronics, 2020, 31, 13646-13656.	2.2	18
9	Characterization of a GaAs/GaAsBi pin solar cell. Semiconductor Science and Technology, 2019, 34, 085001.	2.0	14
10	Negative capacitance phenomena in Au/SrTiO3/p-Si heterojunction structure. Journal of Materials Science: Materials in Electronics, 2020, 31, 8718-8726.	2.2	14
11	Structural, morphological, optical and electrical properties of the Ti doped-ZnO (TZO) thin film prepared by RF sputter technique. Physica B: Condensed Matter, 2021, 616, 413126.	2.7	13
12	Investigation of the effect of annealing on the structural, morphological and optical properties of RF sputtered WO3 nanostructure. Physica B: Condensed Matter, 2021, 622, 413350.	2.7	11
13	Determination of surface morphology and electrical properties of MoO3 layer deposited on GaAs substrate with RF magnetron sputtering. Journal of Materials Science: Materials in Electronics, 2021, 32, 12330-12339.	2.2	9
14	Functional optical design of thickness-optimized transparent conductive dielectric-metal-dielectric plasmonic structure. Scientific Reports, 2022, 12, .	3.3	9
15	V-groove etched 1-eV-GalnNAs nipi solar cell. Applied Physics A: Materials Science and Processing, 2019, 125, 1.	2.3	6
16	Dielectric Properties of Au/SrTiO3/p-Si Structure Obtained by RF Magnetron Sputtering in a Wide Frequency Range. Silicon, 2022, 14, 2717-2722.	3.3	6
17	Effect of different <i>P</i> /As ratio on the optical and structural properties of GaAs _{1â°'<i>x</i>} <i>Pi></i> /GaAs. Surface and Interface Analysis, 2010, 42, 1252-1256.	1.8	5
18	The temperature dependent negative dielectric constant phenomena of Au/n–GaAs structure with CZO interfacial layer. Journal of Materials Science: Materials in Electronics, 2021, 32, 5928-5935.	2.2	4

#	Article	IF	CITATIONS
19	Modeling and Experimental Analysis of Photovoltaic Parameters of GalnP/GaAs Dual Junction p–i–n Solar Cell. Brazilian Journal of Physics, 2021, 51, 553-558.	1.4	3
20	Evaluation of dielectric properties of Au/TZO/n–Si structure depending on frequency and voltage. Journal of Materials Science: Materials in Electronics, 2022, 33, 10516-10523.	2.2	3
21	Influence of V2O5 and B2O3 addition on the sintering behaviour and physical properties of ZnO ceramics. Processing and Application of Ceramics, 2022, 16, 48-54.	0.8	1
22	Investigation of V-groove fabricated GalnNAs nipi solar cell structure. Optical and Quantum Electronics, 2021, 53, 1.	3.3	O